

SPTECH Silicon NPN Power Transistor

2SC3336

DESCRIPTION

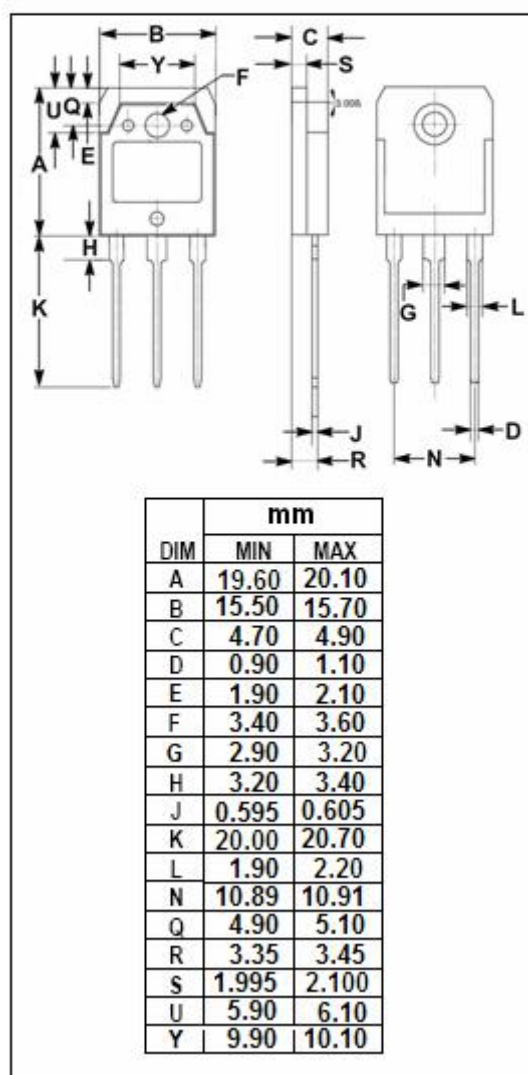
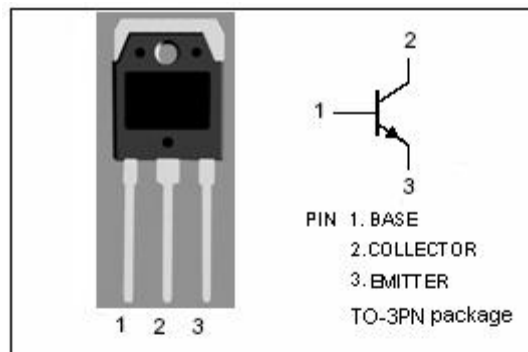
- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = 400V(\text{Min})$
- High Switching Speed

APPLICATIONS

- Designed for high voltage, high speed and high power switching applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	500	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base voltage	10	V
I_C	Collector Current-Continuous	15	A
I_{CM}	Collector Current-Peak	25	A
I_B	Base Current-Continuous	7.5	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	100	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



SPTECH Silicon NPN Power Transistor

2SC3336

ELECTRICAL CHARACTERISTICS

 $T_c=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=20\text{mA}; I_B=0$	400			V
$V_{CEX(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=15\text{A}; I_{B1}=3\text{A}; I_{B2}=-1\text{A}; V_{BE}=-5\text{V}; L=180\mu\text{H}; \text{Clamped}$	400			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=10\text{mA}; I_C=0$	10			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=7.5\text{A}; I_B=1.5\text{A}$			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=7.5\text{A}; I_B=1.5\text{A}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=400\text{V}; I_E=0$			50	μA
I_{CEO}	Collector Cutoff Current	$V_{CE}=350\text{V}; R_{BE}=\infty$			50	μA
h_{FE-1}	DC Current Gain	$I_C=7.5\text{A}; V_{CE}=5\text{V}$	12			
h_{FE-2}	DC Current Gain	$I_C=15\text{A}; V_{CE}=5\text{V}$	5			

Switching times

t_{on}	Turn-on Time	$I_C=15\text{A}, I_{B1}=-I_{B2}=3\text{A}; V_{CC}\approx 250\text{V}$			0.5	μs
t_{stg}	Storage Time				1.5	μs
t_f	Fall Time				0.5	μs